

What is claimed is:

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1. A semiconductor device comprising:
an inter-layer insulating film comprising an organic material formed over
a conductive layer;
5 a first metallic layer formed on said inter-layer insulating film; and
a second metallic layer formed on said first metallic layer,
wherein said conductive layer and said second metallic layer are
connected to each other at the bottom of a contact hole provided in said
inter-layer insulating film.

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2. The semiconductor device according to claim 1, wherein said first
metallic layer is selected from the group consisting of aluminum and a material
predominantly composed of aluminum.

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3. The semiconductor device according to claim 1, wherein said
second metallic layer is selected from the group consisting of titanium and a
material predominantly composed of titanium.

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4. The semiconductor device according to claim 1, wherein said
organic material is an organic-based resin material predominantly selected from
the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and
BCB (benzocyclobutane).

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5. The semiconductor device according to claim 1, wherein said
semiconductor device is selected from the group consisting of an active matrix
liquid-crystal display device, an active matrix EL display device, and an active
matrix EC display device.

semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

5 12. The semiconductor device according to claim 7, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

10 13. A method for fabricating a semiconductor device comprising the steps of:

forming a thin film transistor over a substrate having an insulating surface;

15 forming an inter-layer insulating film comprising an organic material over said thin film transistor;

forming a first metallic film over said inter-layer insulating film;

patterning said first metallic film to form a first metallic layer;

etching said inter-layer insulating film to form contact holes therein by using said first metallic layer as a mask;

20 forming a second metallic film to cover said first metallic layer and said contact holes, and

patterning said first metallic layer and said second metallic film to form wirings, wherein part of said wirings has a multi-layer structure.

25 14. The method for fabricating a semiconductor device according to claim 13, wherein said inorganic film is deposited by a CVD method.

15. The method for fabricating a semiconductor device according to

claim 13, wherein said first metallic film and said second metallic film are deposited by a sputtering method.

16 A method for fabricating a semiconductor device comprising the
5 steps of:

forming a first conductive layer on an insulating surface;

forming an inter-layer insulating film comprising an organic material
over said first conductive layer;

forming a first metallic film over said inter-layer insulating film;

10 patterning said first metallic film to form a first metallic layer;

etching said inter-layer insulating film to form contact holes by using
said first metallic layer as a mask;

forming a second metallic film over said first metallic layer and said
contact holes;

15 forming an inorganic film over said second metallic film;

patterning said first metallic layer, said second metallic film, and said
inorganic film to form wirings having an inorganic layer on the upper surface
thereof, and

forming a second conductive material layer in contact with said wirings
20 to form a capacitor between said wirings and said second material layer with
said inorganic layer as a dielectric substance.

17. The method for fabricating a semiconductor device according to
claim 16, wherein said inorganic film is deposited by a CVD method.

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18. The method for fabricating a semiconductor device according to
claim 16, wherein said first metallic film and said second metallic film are
deposited by a sputtering method.

19. A semiconductor device comprising:
an inter-layer insulating film comprising an organic material formed over
a thin film transistor;

5 a first layer formed on said inter-layer insulating film; and
a second layer formed on said first layer,

wherein a source region or a drain region and said second layer are
connected to each other at the bottom of a contact hole provided in said
inter-layer insulating film,

10 wherein said second layer is contact with said inter-layer insulating film
inside of said contact holes.

20. The semiconductor device according to claim 19, wherein said
first layer is selected from the group consisting of aluminum and a material
15 predominantly composed of aluminum.

21. The semiconductor device according to claim 19, wherein said
second layer is selected from the group consisting of titanium and a material
predominantly composed of titanium.

20 22. The semiconductor device according to claim 19, wherein said
organic material is an organic-based resin material predominantly selected from
the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and
BCB (benzocyclobutane).

25 23. The semiconductor device according to claim 19, wherein said
semiconductor device is selected from the group consisting of an active matrix
liquid-crystal display device, an active matrix EL display device, and an active

matrix EC display device.

24. The semiconductor device according to claim 19, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

25. A method for fabricating a semiconductor device comprising the steps of:

forming a thin film transistor over a substrate having an insulating surface;

forming an inter-layer insulating film comprising an organic material over said thin film transistor;

forming a first layer over said inter-layer insulating film;

forming contact holes in said inter-layer insulating film by etching said inter-layer insulating;

forming a second layer over said first layer and said contact holes; and

patterning said first layer and said second layer to form wirings, wherein part of said wirings has a multi-layer structure.

26. The method for fabricating a semiconductor device according to claim 25, wherein said inorganic film is deposited by a CVD method.

27. The method for fabricating a semiconductor device according to claim 25, wherein said first layer and said second layer are deposited by a sputtering method.

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